

<b>SANYO</b>	No.4220	<b>2SJ284</b>
		P-Channel MOS Silicon FET Very High-Speed Switching Applications

**Features**

- Low ON resistance.
- Very high-speed switching.
- Low-voltage drive.

**Absolute Maximum Ratings at Ta = 25°C**

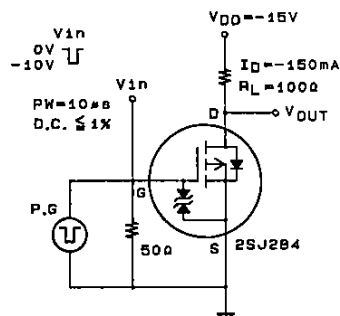
		unit
Drain to Source Voltage	V <sub>DSS</sub>	-30 V
Gate to Source Voltage	V <sub>GSS</sub>	±15 V
Drain Current(DC)	I <sub>D</sub>	-300 mA
Drain Current(Pulse)	I <sub>DP</sub>	-1.2 A
Allowable Power Dissipation	P <sub>D</sub>	250 mW
Channel Temperature	T <sub>ch</sub>	150 °C
Storage Temperature	T <sub>stg</sub>	-55 to +150 °C

*PW ≤ 10 μs, duty cycle ≤ 1%*

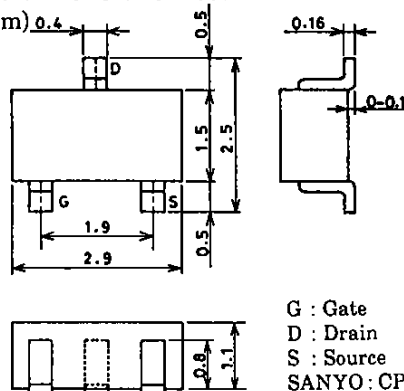
**Electrical Characteristics at Ta = 25°C**

			min	typ	max	unit
D-S Breakdown Voltage	V <sub>(BR)DSS</sub>	I <sub>D</sub> = -1mA, V <sub>GS</sub> = 0	-30			V
Zero Gate Voltage Drain Current	I <sub>DSS</sub>	V <sub>DS</sub> = -30V, V <sub>GS</sub> = 0			-100	μA
Gate to Source Leakage Current	I <sub>GSS</sub>	V <sub>GS</sub> = ±12V, V <sub>DS</sub> = 0			±10	μA
Cutoff Voltage	V <sub>GS(off)</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -1mA	-1.0		-2.0	V
Forward Transfer Admittance	Y <sub>fs</sub>	V <sub>DS</sub> = -10V, I <sub>D</sub> = -150mA	200	350		mS
Static Drain to Source on State Resistance	R <sub>DSS(on)</sub>	I <sub>D</sub> = -150mA, V <sub>GS</sub> = -10V		1.5	2.2	Ω
	R <sub>DS(on)</sub>	I <sub>D</sub> = -150mA, V <sub>GS</sub> = -4V		2.2	3.3	Ω
Input Capacitance	C <sub>iss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		50		pF
Output Capacitance	C <sub>oss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		35		pF
Reverse Transfer Capacitance	C <sub>rss</sub>	V <sub>DS</sub> = -10V, f = 1MHz		10		pF
Turn-ON Delay Time	t <sub>d(on)</sub>	See specified Test Circuit.		7		ns
Rise Time	t <sub>r</sub>	∕		10		ns
Turn-OFF Delay Time	t <sub>d(off)</sub>	∕		40		ns
Fall Time	t <sub>f</sub>	∕		30		ns
Diode Forward Voltage	V <sub>SD</sub>	I <sub>S</sub> = -300mA, V <sub>GS</sub> = 0	-1			V

Marking : AM

**Switching Time Test Circuit****Package Dimensions 2091**

(unit : mm)

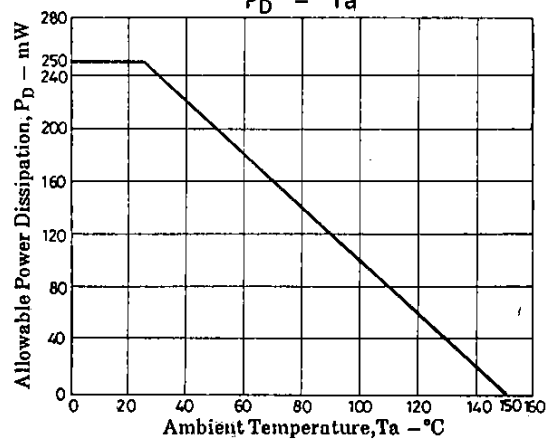
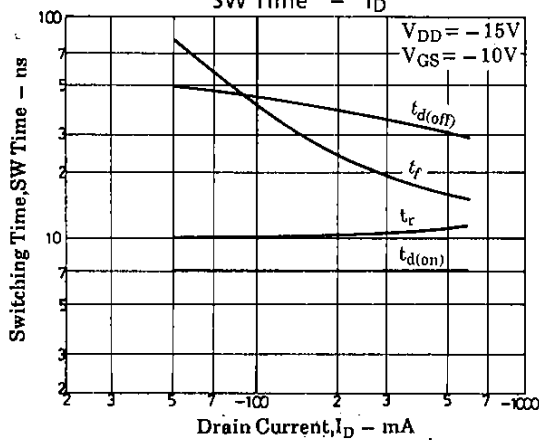
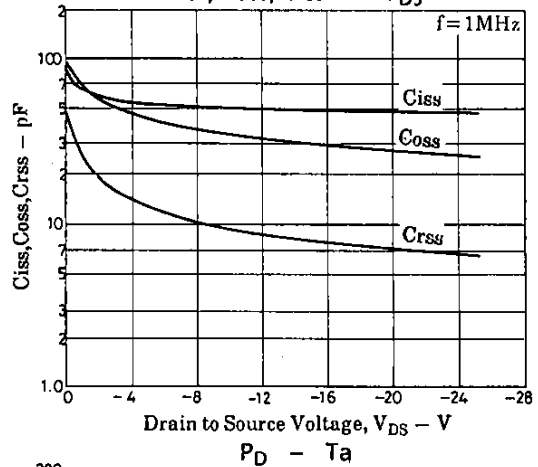
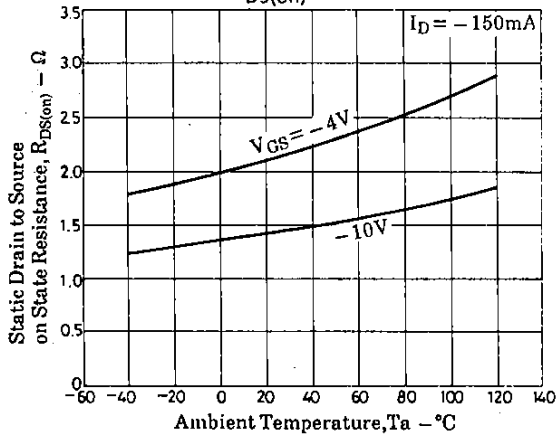
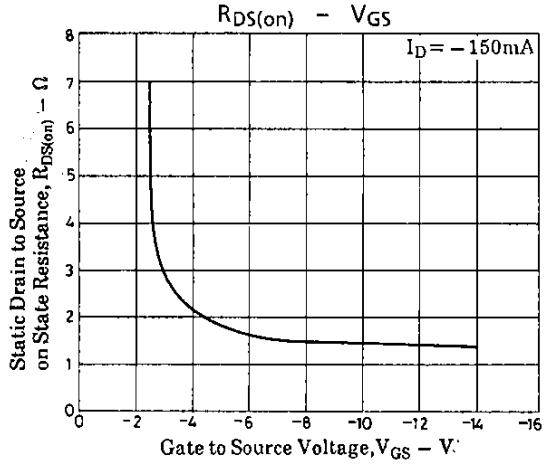
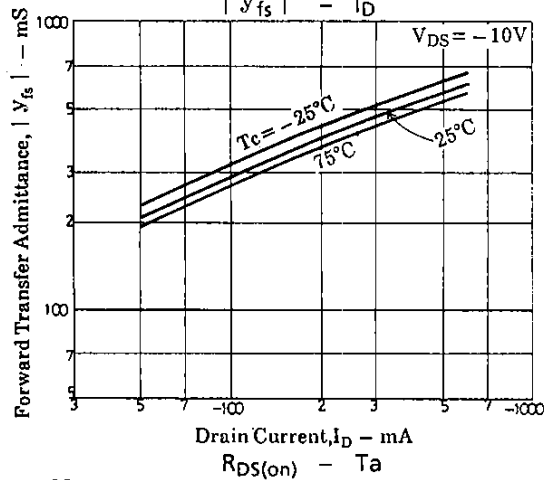
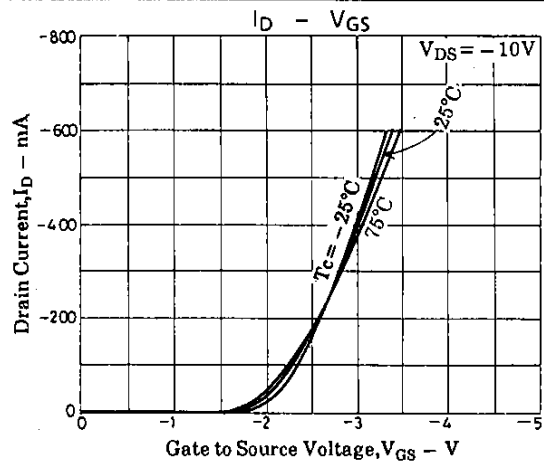
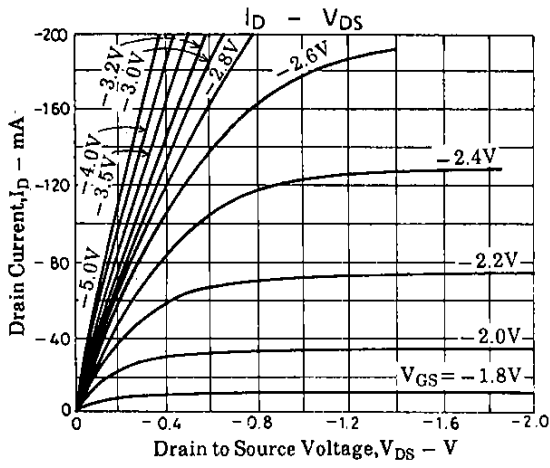


G : Gate  
D : Drain  
S : Source  
SANYO : CP

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